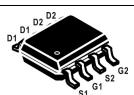
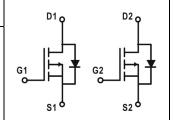
V_{DSS}, -30V

 $R_{DS(ON)}$, $60m\Omega$ (max.) @ $V_{GS}\text{=-}10V$ $R_{DS(ON)}$, $90m\Omega$ (max.) @ $V_{GS}\text{=-}4.5V$

 I_D , -5A







Description

The SG4953S is the highest performance trench P-Ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The SG4953S meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Low On-Resistance
 - Low Input Capacitance
- Low Miller Charge
- · Low Input/Output Leakage

Applications

- Motor / Body Load Control
- Automotive Systems
- Load Switch
- · DC-DC converters and Off-line UPS

Ordering Informatio	n				
Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG4953S	Halogen-Free	SOP-8	S	Tape & Reel	2,500

Absolute Maximum Ratings (T _A =25°C unless otherwise noted)							
Paramete	r	Symbol	Value	Unit			
Drain-Source Voltage		V _{DS}	-30	V			
Gate-Source Voltage		V _{GS}	±20	V			
Drain Current-Continuous	T _C =25°C	I-	-5	А			
Drain Current-Continuous	T _C =70°C	I _D	-3.9	А			
Drain Current-Pulsed Note 1		I _{DM}	-20	А			
Danie Comment Continuous	T _A =25°C		-4.2	А			
Drain Current-Continuous	T _A =70°C	I _D	-3.3	А			
Avalanche Current, L=0.1mH		l _{AS}	-15	А			
Avalanche Energy, L=0.1mH		E _{AS}	11.25	mJ			
	T _C =25°C		2.1	W			
Maximum Dawer Dissipation	T _C =70°C	P _D	1.3	W			
Maximum Power Dissipation	T _A =25°C	r _D	1.5	W			
	T _A =70°C		0.9	W			
Storage Temperature Range	T _{STG}	-55 to +150	°C				
Operating Junction Temperature Range		T _J	-55 to +150	°C			

Thermal Resistance Ratings						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 2	$R_{\theta JA}$	Steady State	-	-	85	°C/W
Maximum Junction-to-Case Note 2	R ₀ JC	Steady State	-	-	60	°C/W



Electrical Characteristics (T」=25°C unless otherwise noted)							
OFF CHARACTERISTICS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =-250μA	-30	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V	-	-	-1	μA	
Gate-Body Leakage	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA	

ON CHARACTERISTICS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Gate Threshold Voltage	V _{GS(TH)}	$V_{DS}=V_{GS}$, $I_{DS}=-250\mu A$	-1	-	-3	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _{DS} =-5A	-	45	60		
Dialii-Source Oil-State Resistance		V _{GS} =-4.5V, I _{DS} =-4A	-	66	90	mΩ	

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C _{iss}		-	680	-	
Output Capacitance	Coss	V _{DS} =-15V, V _{GS} =0V, f=1MHz	-	290	-	рF
Reverse Transfer Capacitance	C _{rss}	C _{rss}	-	120	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	10	-	
Rise Time	t _r	V_{DD} =-15V, V_{GS} =-10V, R_G =3.3 Ω , I_D =-5A	-	17	-	ns
Turn-Off Delay Time	$T_{d(off)}$		-	22	-	
Fall Time	t _f		-	21	-	
Total Gate Charge at -4.5V	Qg	\\ - 45\\ \\ - 45\\	-	6.5	-	
Gate to Source Gate Charge	Q_{gs}	V_{DS} =-15V, V_{GS} =-4.5V, I_{D} =-5A	-	2.8	-	nC
Gate to Drain "Miller" Charge	Q_gd	ID274	-	3	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter Symbol		Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS} =0V, I_{S} =-5A	-	-	-1.3	V
Body Diode Reverse Recovery Time	t _{rr}		-	12	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	3.5	-	nC

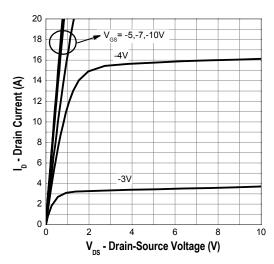
Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design. R_{θJA} shown below for single device operation on FR-4 in still air.

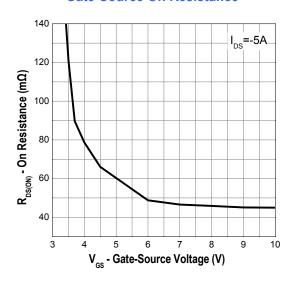
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Typical Operating Characteristics

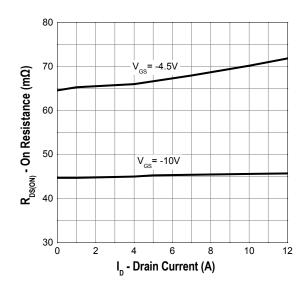
Output Characteristics



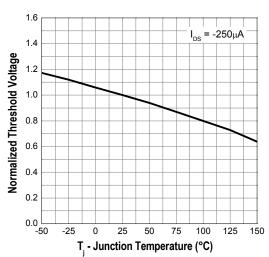
Gate-Source On Resistance



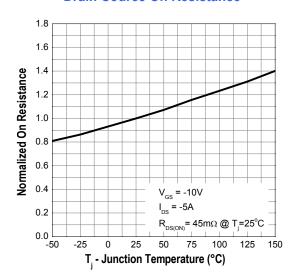
Drain-Source On Resistance



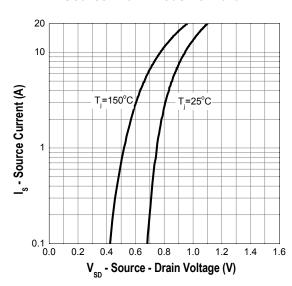
Gate Threshold Voltage



Drain-Source On Resistance

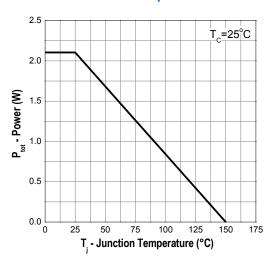


Source-Drain Diode Forward

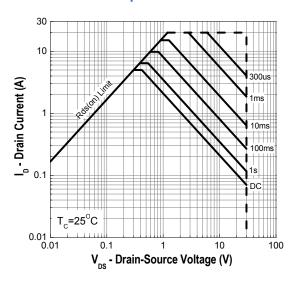


Typical Operating Characteristics (Cont.)

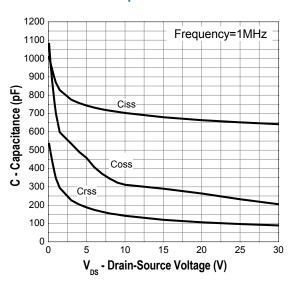
Power Dissipation



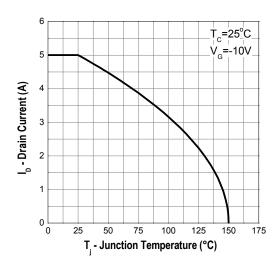
Safe Operation Area



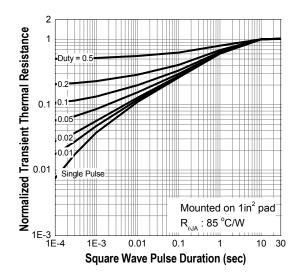
Capacitance



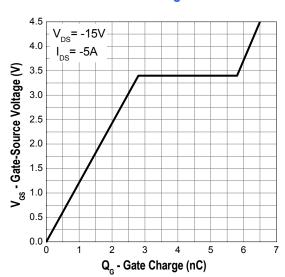
Drain Current



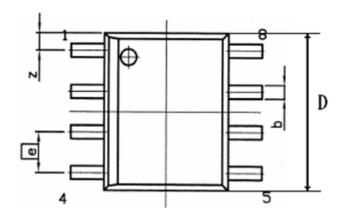
Transient Thermal Impedance

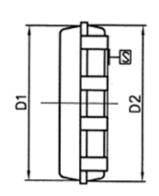


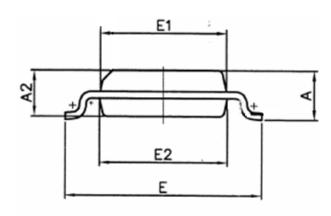
Gate Charge

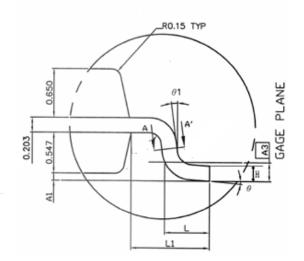


SOP-8 Dimensions









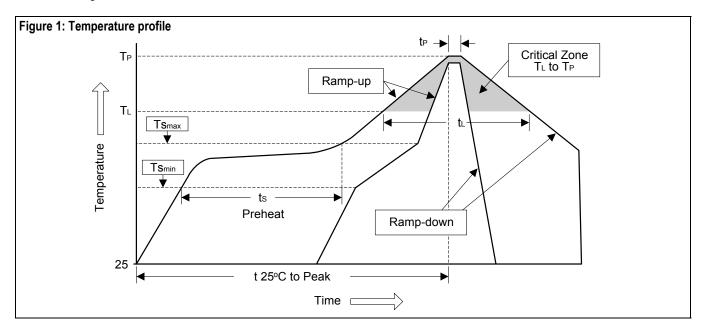
DETAIL A

SOP-8 Dimensions						
Cumbala		Millimeters		Inches		
Symbols	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	1.35	1.55	1.753	0.053	0.061	0.069
A1	0.10	0.15	0.25	0.004	0.006	0.010
A2	1.27	1.52	1.626	0.050	0.060	0.064
A3	•	0.254	-	-	0.010	-
b	0.30	0.40	0.51	0.012	0.016	0.020
D	4.70	4.90	5.10	0.185	0.193	0.201
D1	4.70	4.90	5.00	0.185	0.193	0.197
D2	4.80	4.90	5.00	0.189	0.193	0.197
E	5.79	6.00	6.20	0.228	0.236	0.244
E1	3.75	3.90	4.00	0.148	0.154	0.157
E2	3.75	3.90	4.00	0.148	0.154	0.157
Н	0.17	0.21	0.25	0.007	0.008	0.010
е	-	1.27	-	-	0.050	-
L	0.40	0.76	1.27	0.016	0.030	0.050
L1	0.95	1.05	1.15	0.037	0.041	0.045
θ	0°	4°	8°	0°	4°	8°
θ1	0°	-	•	0°	-	_



Soldering Methods for SiliconGear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly		
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec		
Preheat				
- Temperature Min (Ts _{min})	100°C	150°C		
- Temperature Max (Ts _{max})	150°C	200°C		
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec		
Tsmax to T _L				
- Ramp-up Rate	<3°C/sec	<3°C/sec		
Time maintained above:				
- Temperature (T _L)	183°C	217°C		
- Time (t∟)	60 to 150 sec	60 to 150 sec		
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C		
Time within 5°C of actual Peak Temperature (t _P)	10 to 30 sec	20 to 40 sec		
1 ()	<6°C/222	∠G°C/ooo		
Ramp-down Rate	<6°C/sec	<6°C/sec		
Time 25°C to Peak Temperature	<6 minutes	<8 minutes		

3. Flow (wave) soldering (solder dipping)

	Products	Peak Temperature	Dipping Time		
	Pb devices.	245°C ±5°C	5sec ±1sec		
Pb-Free devices.		260°C +0/-5°C	5sec ±1sec		



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